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- Independent Asynchronous Inputs and Outputs
- Low-Power Advanced CMOS Technology
- Bidirectional
- Dual 1024 by 9 Bits
- Programmable Almost-Full/Almost-Empty Flag
- Empty, Full, and Half-Full Flags

- Access Times of 25 ns With a 50-pF Load
- Data Rates up to 50 MHz
- Fall-Through Times of 22 ns Maximum
- High Output Drive for Direct Bus Interface
- Package Options Include 44-Pin Plastic Leaded Chip Carriers (FN) and 64-Pin Thin Quad Flat (PAG, PM) Packages

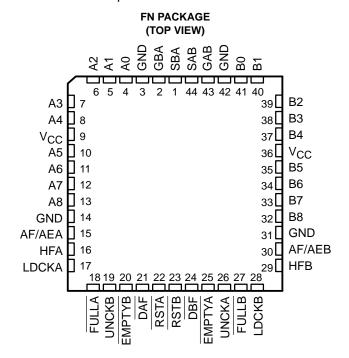
description

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ACT2235 is arranged as two 1024×9 -bit FIFOs for high speed and fast access times. It processes data at rates up to 50 MHz, with access times of 25 ns in a bit-parallel format.

The SN74ACT2235 consists of bus-transceiver circuits, two 1024×9 -bit FIFOs, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal FIFO memories. Enable (GAB and GBA) inputs are provided to control the transceiver functions. The select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 2 shows the eight fundamental bus-management functions that can be performed with the SN74ACT2235.

For more information on this device family, see the application report, $1K \times 9 \times 2$ Asynchronous FIFO SN74ACT2235, literature number SCAA010.

The SN74ACT2235 is characterized for operation from 0°C to 70°C.

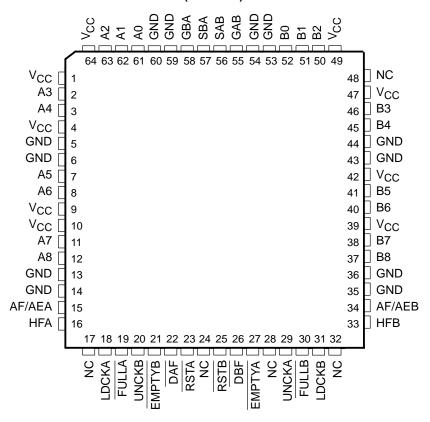




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PAG OR PM PACKAGE (TOP VIEW)

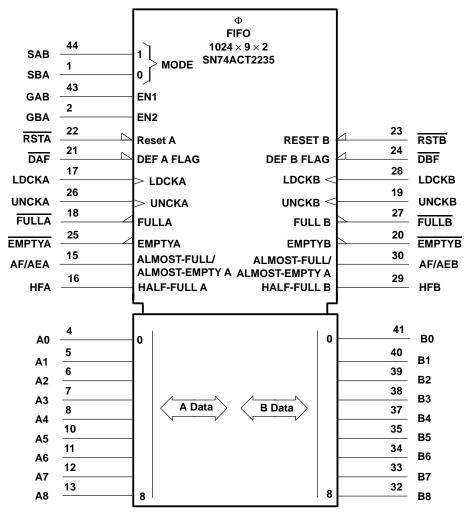


NC - No internal connection



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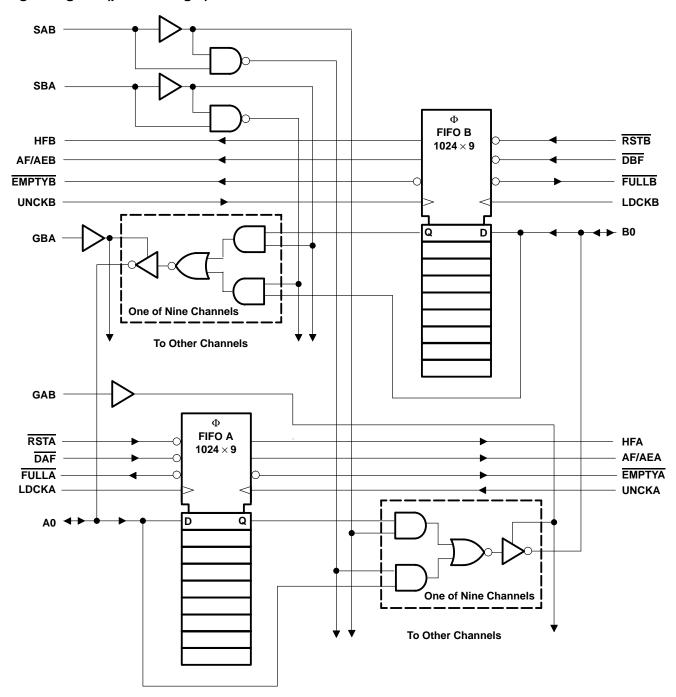
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the FN package.

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logic diagram (positive logic)





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Terminal Functions

TERMINAL [†]		1/0	DESCRIPTION						
NAME	NO.	2	DESCRIPTION						
AF/AEA AF/AEB	15 30	0	Almost full/almost empty flags. The almost-full/almost-empty A flag (AF/AEA) is defined by the almost-full/almost-empty offset value for FIFO A (X). AF/AEA is high when FIFO A contains X or fewer words or 1024 – X words. AF/AEA is low when FIFO A contains between (X + 1) or (1023 – X) words. The operation of the almost-full/almost-empty B flag (AF/AEB) is the same as AF/AEA for FIFO B.						
A0–A8	4–8, 10–13	I /O	A-data inputs and outputs						
B0-B8	32–35, 37–41	I/O	B-data inputs and outputs						
DAF DBF	21 24	I	Define-flag inputs. The high-to-low transition of \overline{DAF} stores the binary value on A0–A8 as the almost-full/almost-empty offset value for FIFO A (X). The high-to-low transition of \overline{DBF} stores the binary value of B0–B8 as the almost-full/almost-empty offset value for FIFO B (Y).						
EMPTYA EMPTYB	25 20	0	Empty flags. EMPTYA and EMPTYB are low when their corresponding memories are empty and high when they are not empty.						
FULLA FULLB	18 27	0	Full flags. FULLA and FULLB are low when their corresponding memories are full and high when they are not full.						
HFA HFB	16 29	0	Half-full flags. HFA and HFB are high when their corresponding memories contain 512 or more words and low when they contain 511 or fewer words.						
LDCKA LDCKB	17 28	I	Load clocks. Data on A0–A8 is written into FIFO A on a low-to-high transition of LDCKA. Data on B0–B8 is written into FIFO B on a low-to-high transition of LDCKB. When the FIFOs are full, LDCKA and LDCKB have no effect on the data residing in memory.						
GAB GBA	43 2	_	Output enables. GAB, GBA control the transceiver functions. When GBA is low, A0–A8 are in the high-impedance state. When GAB is low, B0–B8 are in the high-impedance state.						
RSTA RSTB	22 23	_	Reset. A reset is accomplished in each direction by taking RSTA and RSTB low. This sets EMPTYA, EMPTYB, FULLA, FULLB, and AF/AEB high. Both FIFOs must be reset upon power up.						
SAB SBA	44 1	L	Select-control inputs. SAB and SBA select whether real-time or stored data is transferred. A low level selects real-time data and a high level selects stored data. Eight fundamental bus-management functions can be performed as shown in Figure 2.						
UNCKA UNCKB	26 19	I	Unload clocks. Data in FIFO A is read to B0–B8 on a low-to-high transition of UNCKA. Data in FIFO B is read to A0–A8 on a low-to-high transition of UNCKB. When the FIFOs are empty, UNCKA and UNCKB have no effect on data residing in memory.						

[†] Terminals listed are for the FN package.

programming procedure for AF/AEA

The almost-full/almost-empty flags (AF/AEA, AF/AEB) are programmed during each reset cycle. The almost-full/almost-empty offset value for FIFO A (X) and for FIFO B (Y) is either a user-defined value or the default values of X = 256 and Y = 256. Below are instructions to program AF/AEA using both methods. AF/AEB is programmed in the same manner for FIFO B.

user-defined X

Take \overline{DAF} from high to low. This stores A0–A8 as X.

If RSTA is not already low, take RSTA low.

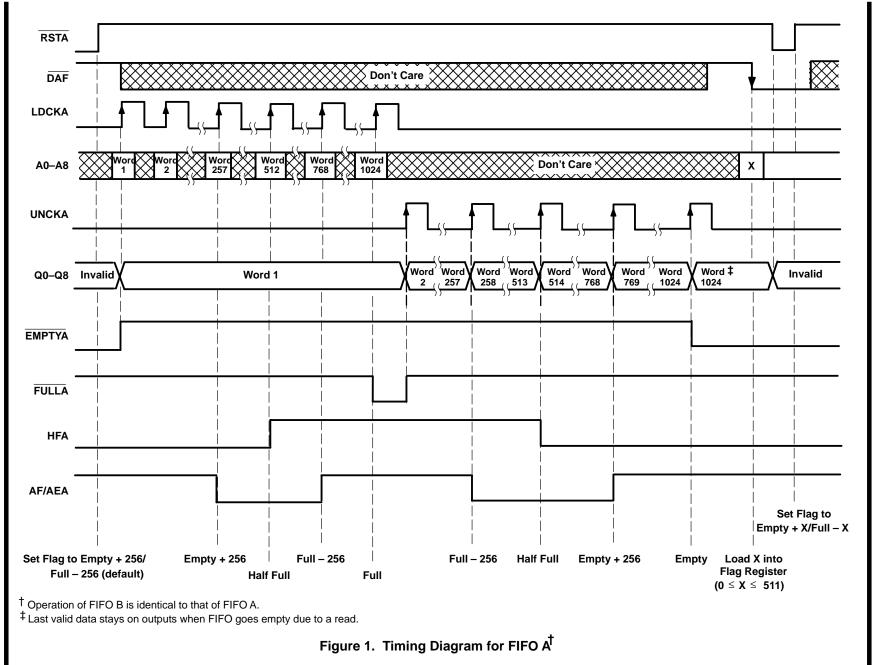
With DAF held low, take RSTA high. This defines AF/AEA using X.

To retain the current offset for the next reset, keep $\overline{\mathsf{DAF}}$ low.

default X

To redefine AF/AE using the default value of X = 256, hold \overline{DAF} high during the reset cycle.





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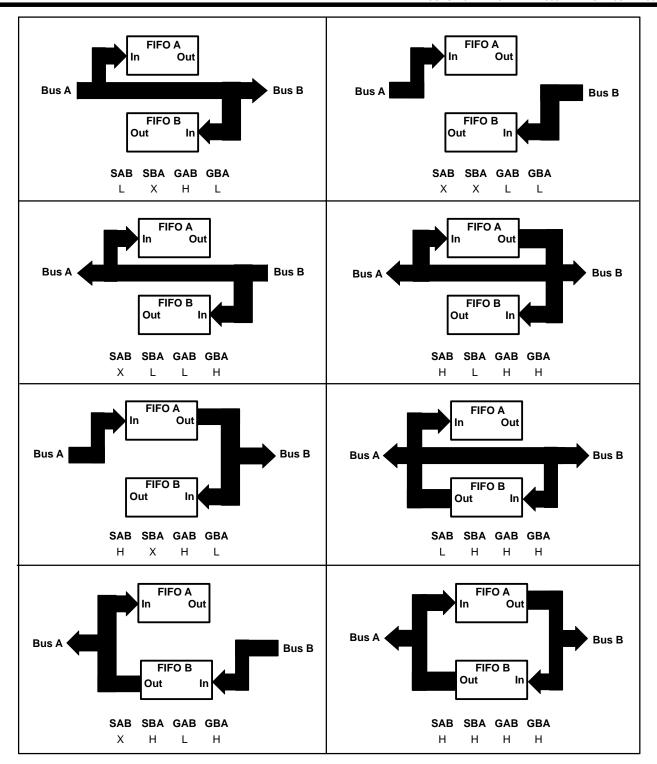


Figure 2. Bus-Management Functions



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SELECT-MODE CONTROL

CON	rol	OPERATION					
SAB	SBA	A BUS	B BUS				
L	L	Real-time B to A bus	Real-time A to B bus				
L	Н	FIFO B to A bus	Real-time A to B bus				
Н	L	Real-time B to A bus	FIFO A to B bus				
н	Н	FIFO B to A bus	FIFO A to B bus				

OUTPUT-ENABLE CONTROL

CON	ΓROL	OPERATION					
GAB	GBA	A BUS	B BUS				
Н	Н	A bus enabled	B bus enabled				
L	Н	A bus enabled	Isolation/input to B bus				
Н	L	Isolation/input to A bus	B bus enabled				
L	L	Isolation/input to A bus	Isolation/input to B bus				

Figure 2. Bus-Management Functions (Continued)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	–0.5 V to 7 V
Input voltage range, V _I : Control inputs	–0.5 V to 7 V
I/O ports	–0.5 V to 5.5 V
Voltage range applied to a disabled 3-state output	5.5 V
Package thermal impedance, θ _{JA} (see Note 1): FN package	46°C/W
PAG package	58°C/W
PM package	67°C/W
Storage temperature range, T _{stq}	–65°C to 150°C
Maximum junction temperature, T _J	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions

				ACT2235-20		ACT2235-30		ACT2235-40		ACT2235-60	
				MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage			5.5	4.5	5.5	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage				2		2		2		V
V _{IL}	Low-level input voltage			0.8		0.8		0.8		0.8	V
la	High level output ourrent	A or B ports		-8		-8		-8		-8	A
ЮН	High-level output current	Status flags		-8		-8		-8		-8	mA
1	Low lovel output output	A or B ports		16		16		16		16	A
lOL	Low-level output current	Status flags		8		8		8		8	mA
TA	Operating free-air temperature			70	0	70	0	70	0	70	°C



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER		TEST CONDITION	ONS	MIN	TYP†	MAX	UNIT
Vон		$V_{CC} = 4.5 \text{ V},$	IOH = -8 mA		2.4			V
Vai	Flags	$V_{CC} = 4.5 \text{ V},$	$I_{OL} = 8 \text{ mA}$				0.5	V
VOL	I/O ports	$V_{CC} = 4.5 \text{ V},$	$I_{OL} = 16 \text{ mA}$				0.5	V
Ц		$V_{CC} = 5.5 \text{ V},$	VI = ACC or 0				±5	μΑ
loz		$V_{CC} = 5.5 \text{ V},$	VO = VCC or 0				±5	μΑ
lcc [‡]		$V_{I} = V_{CC} - 0.2 \text{ V}$	or 0			10	400	μΑ
Δlcc§		$V_{CC} = 5.5 V$,	One input at 3.4 V,	Other inputs at V _{CC} or GND			1	mA
Ci		V _I = 0,	f = 1 MHz			4		pF
Co		V _O = 0,	f = 1 MHz			8		pF

timing requirements over recommended operating conditions (unless otherwise noted) (see Figure 3)

			'ACT2235-20		'ACT22	235-30	'ACT2235-40		'ACT2235-60		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNII
follow Clock frequency		LDCKA or LDCKB		50		33		25		16.7	MHz
Iclock	f _{clock} Clock frequency	UNCKA or UNCKB		50		33		25		16.7	MHZ
		RSTA or RSTB low	20		20		25		25		
		LDCKA or LDCKB low	8		10		14		20		
١.	Pulse duration	LDCKA or LDCKB high	8		10		14		20		ns
t _W	ruise duration	UNCKA or UNCKB low	8		10		14		20		115
		UNCKA or UNCKB high	8		10		14		20		
		DAF or DBF high	10		10		10		10		
		Data before LDCKA or LDCKB↑	4		4		5		5		
	Setup time	Define AF/AE: D0–D8 before DAF or DBF↓	5		5		5		5		
t _{su}		Define AF/AE: DAF or DBF↓ before RSTA or RSTB↑	7		7		7		7		ns
		Define AF/AE (default): DAF or DBF high before RSTA or RSTB↑	5		5		5		5		
		RSTA or RSTB inactive (high) before LDCKA or LDCKB↑	5		5		5		5		
		Data after LDCKA or LDCKB↑	1		1		2		2		
		Define AF/AE: D0–D8 after DAF or DBF↓	0		0		0		0		
^t h	Hold time	Define AF/AE: DAF or DBF low after RSTA or RSTB↑	0		0		0		0		ns
		Define AF/AE (default): DAF or DBF high after RSTA or RSTB↑	0		0		0		0		



[†] All typical values are at V_{CC} = 5 V, T_A = 25°C. ‡ I_{CC} is tested with outputs open. § This is the supply current when each input is at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM	то	'A	CT2235-2	20	'ACT22	235-30	'ACT22	235-40	'ACT22	235-60	UNIT
PARAMETER	(INPUT)	(OUTPUT)	MIN	TYP [†]	MAX	MIN	MAX	MIN	MAX	MIN	MAX	ONIT
f	LDCK		50			33		25		16.7		MHz
fmax	UNCK		50			33		25		16.7		IVII IZ
	LDCK↑, LDCKB↑	B or A	8		22	8	22	8	24	8	26	ns
^t pd	UNCKA↑, UNCKB↑	DOIA	12	17	25	12	25	12	35	12	45	115
^t PLH	LDCK↑, LDCKB↑	EMPTYA, EMPTYB	4		15	4	15	4	17	4	19	ns
	UNCKA↑, UNCKB↑	EMPTYA, EMPTYB	2		17	2	17	2	19	2	21	
t _{PHL}	RSTA↓, RSTB↓	CIVIFITE	2		18	2	18	2	20	2	22	ns
	LDCK↑, LDCKB↑	FULLA, FULLB	4		15	4	15	4	17	4	19	
	UNCKA↑, UNCKB↑	FULLA, FULLB	4		15	4	15	4	17	4	19	
	RSTA↓, RSTB↓	FULLA, FULLB	2		15	2	15	2	17	2	19	
^t PLH		AF/AEA, AF/AEB	2		15	2	15	2	17	2	19	ns
	LDCK↑, LDCKB↑	HFA, HFB	2		15	2	15	2	17	2	19	
^t PHL	UNCKA↑, UNCKB↑	HFA, HFB	4		18	4	18	4	20	4	22	ns
	RSTA↓, RSTB↓		1		15	1	15	1	17	1	19	
	SAB or SBA‡	B or A	1		11	1	11	1	12	1	14	
	A or B	BOIA	1		11	1	11	1	12	1	14	
t _{pd}	LDCK↑, LDCKB↑	AF/AEA,	2		18	2	18	2	20	2	22	ns
	UNCKA↑, UNCKB↑	AF/AEB	2		18	2	18	2	20	2	22	
t _{en}	GBA or GAB	A or B	2		11	2	11	2	13	2	15	ns
^t dis	GBA or GAB	A or B	1		9	1	9	1	11	1	13	ns

operating characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

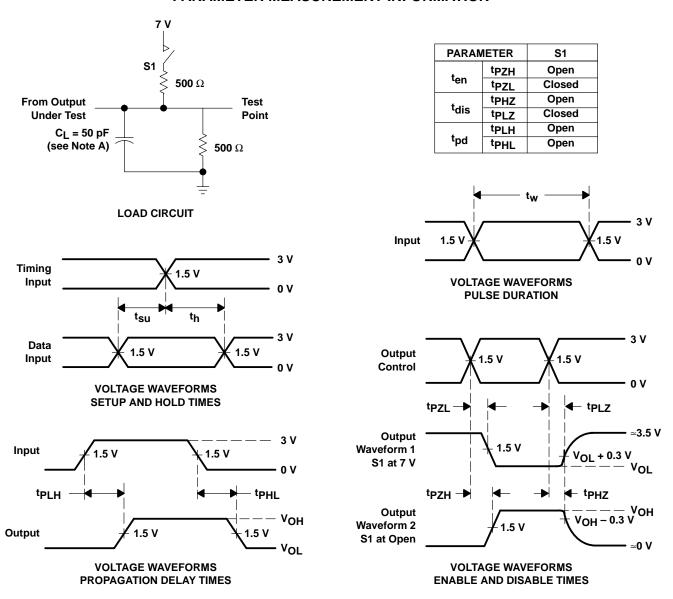
	PARAMETER	TEST CO	TYP	UNIT		
C _{pd}	Down dissination conscitones per 4K hite	Outputs enabled	C. 50 pF	4 E MI I-	71	pF
	Power dissipation capacitance per 1K bits	Outputs disabled	$C_L = 50 \text{ pF},$	f = 5 MHz	57	



[†] All typical values are at V_{CC} = 5 V, T_A = 25°C. ‡ These parameters are measured with the internal output state of the storage register opposite that of the bus input.

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PARAMETER MEASUREMENT INFORMATION

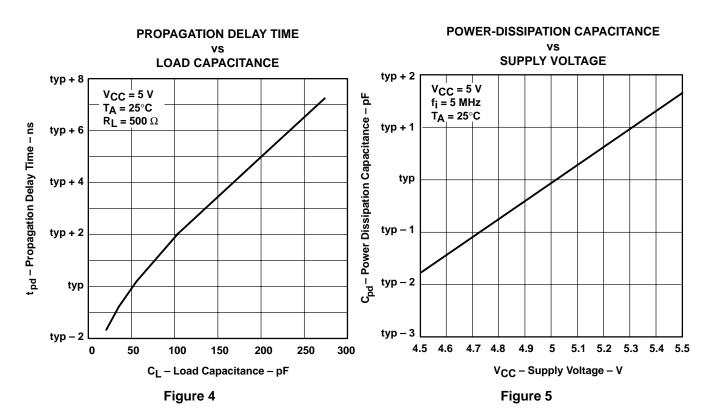


NOTE A: C_L includes probe and jig capacitance.

Figure 3. Load Circuit and Voltage Waveforms



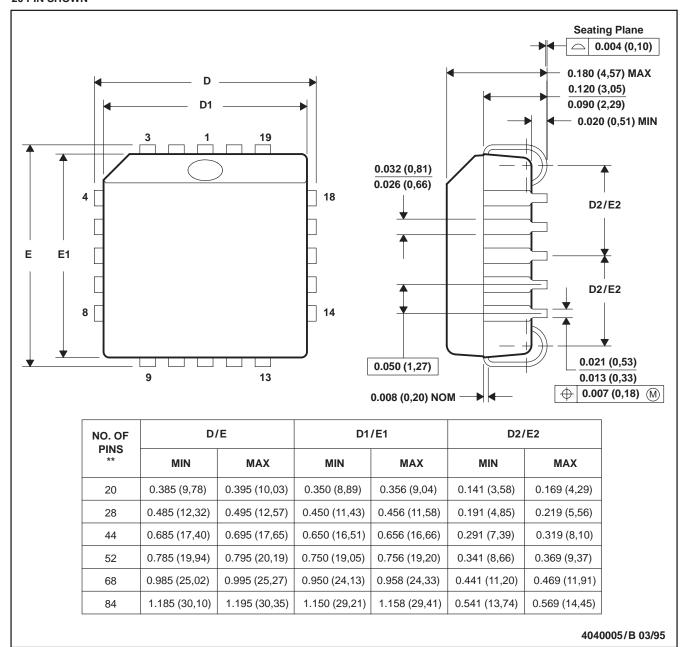
TYPICAL CHARACTERISTICS



FN (S-PQCC-J**)

20 PIN SHOWN

PLASTIC J-LEADED CHIP CARRIER



NOTES: A. All linear dimensions are in inches (millimeters).

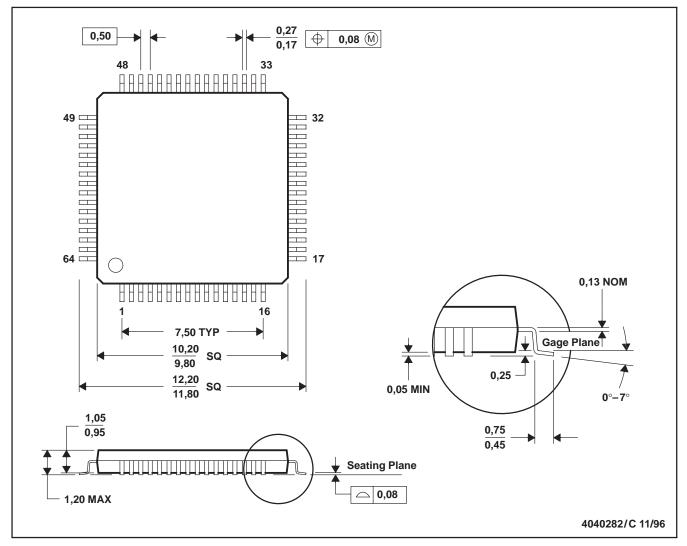
B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-018

PAG (S-PQFP-G64)

PLASTIC QUAD FLATPACK

1



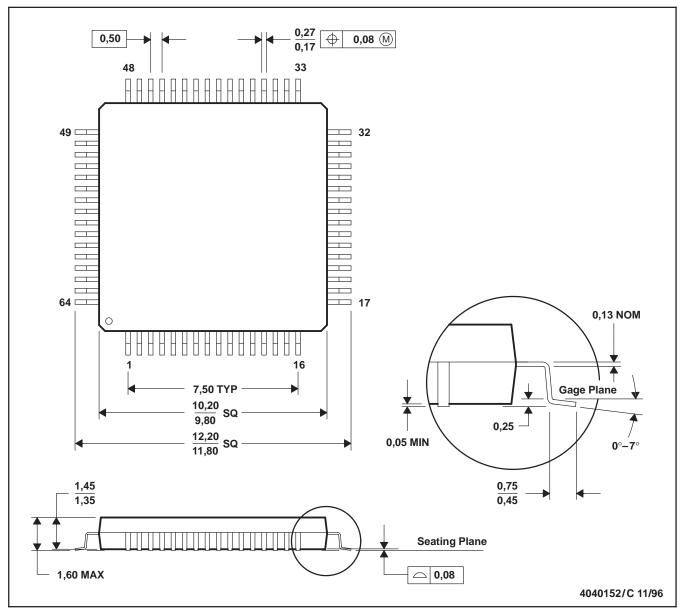
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-026

PM (S-PQFP-G64)

PLASTIC QUAD FLATPACK

1



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-026
- D. May also be thermally enhanced plastic with leads connected to the die pads.

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